

CT25AS-8

STROBE FLASHER USE

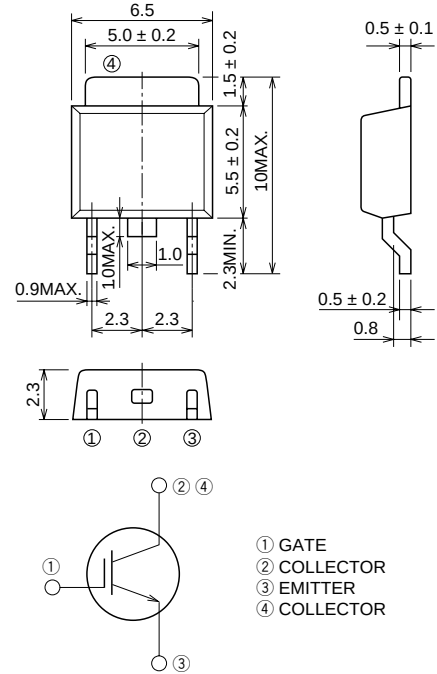
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- V_{CES} 400V
- I_{CM} 150A

OUTLINE DRAWING

Dimensions in mm



MP-3

APPLICATION

Strobe Flasher.

MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V$	400	V
V_{GES}	Gate-emitter voltage	$V_{CE} = 0V$, See notice 4	± 30	V
V_{GEM}	Peak gate-emitter voltage	$V_{CE} = 0V$, $t_w = 0.5s$	± 40	V
I_{CM}	Collector current (Pulsed)	See figure 1	150	A
T_j	Junction temperature		$-40 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-40 \sim +150$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$I_C = 1mA$, $V_{GE} = 0V$	450	—	—	V
I_{CES}	Collector-emitter leakage current	$V_{CE} = 400V$, $V_{GE} = 0V$	—	—	10	μA
I_{GES}	Gate-emitter leakage current	$V_{GE} = \pm 40V$, $V_{CE} = 0V$	—	—	± 0.1	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{CE} = 10V$, $I_C = 1mA$	—	—	7.0	V

PERFORMANCE CURVES

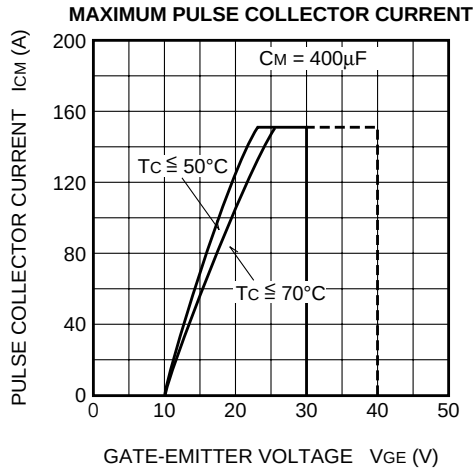
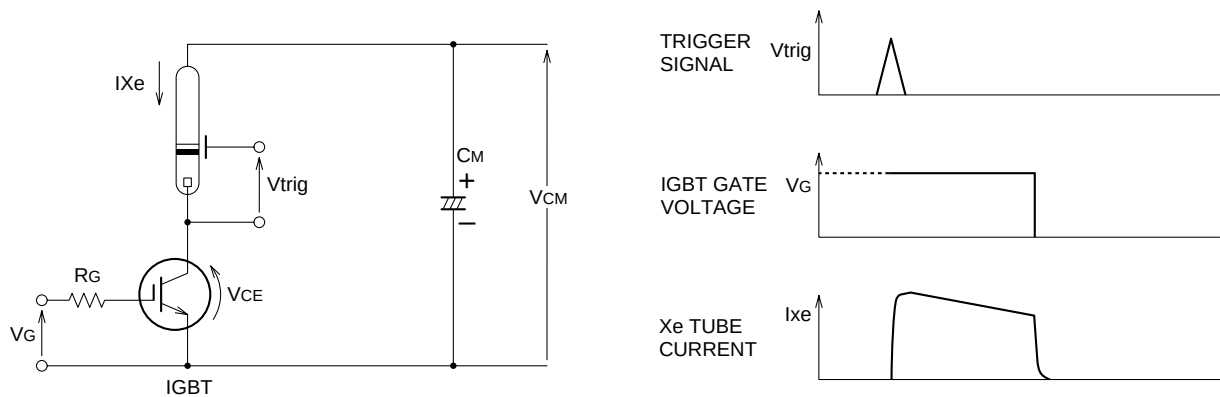


Figure 1

APPLICATION EXAMPLE



RECOMMEND CONDITION	MAXIMUM CONDITION
$V_{CM} = 330V$	350V
$I_P = 130A$	150A
$C_M = 300\mu F$	400μF
$V_{GE} = 28V$	

Notice 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current.
And reverse gate current during turn-off must be kept less than 1A.
(In general, it is satisfied if $R_G \geq 30\Omega$)

Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide.
So please handle carefully not to suffer from electrostatic charge.

Notice 3. The operation life should be endured 5,000 shots under the charge current ($I_{Xe} \leq 150A$: full luminescence condition) of main condenser ($C_M=400\mu F$).
Repetition period under full luminescence condition is over 3 seconds.

Notice 4. Total operation hours must be applied within 5,000 hours.